

What Is Claimed Is:

1. A micro inertia sensor comprising

a lower glass substrate;

a lower silicon including a first border, a first fixed
5 point and a side movement sensing structure;

an upper silicon including a second border, a second
fixed point being connected to a via hole, in which a metal
wiring is formed, on an upper side, and a sensing electrode,
which correspond to the first border, the first fixed point and
10 the side movement sensing structure;

a bonded layer by a eutectic bonding between the upper
silicon and the lower silicon; and

an upper glass substrate, being positioned on an upper
portion of the upper silicon, for providing the via hole on
15 which an electric conduction wiring is formed.

2. The micro inertia sensor according to claim 1, wherein
the side movement sensing structure comprises a structure being
movable in a horizontal direction and an sensing electrode for
20 sensing a variation of a capacity as the structure horizontally
moves.

